

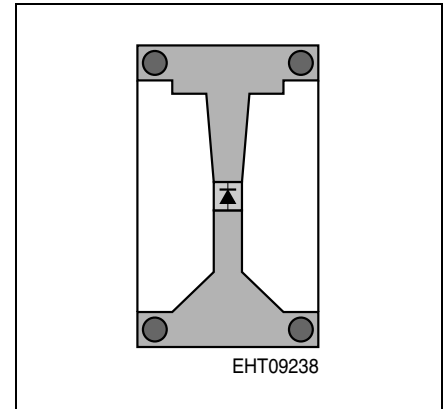


Silicon Single Flip Chip Schottky Diode

BAT 14-077S

Preliminary Data Sheet

- Single Schottky medium Barrier Mixer Diode
- For W-band application up to 80 GHz



ESD: Electrostatic discharge sensitive device, observe handling precautions!

Type	Marking	Ordering Code	Pin Configuration			Package
BAT 14-077S	–	Q62702-D1353	–	–	–	FLIP CHIP 1

Maximum Ratings

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	3	V
Forward current	I_F	25	mA
Total power dissipation ($T_S = 25\text{ °C}$)	P_{tot}	20	mW
Junction temperature	T_j	150	°C
Operating temperature range	T_{op}	– 40 ... + 150	°C
Storage temperature	T_{stg}	– 55 ... + 150	°C

Electrical Characteristics at $T_A = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Limit Values			Unit	Test Conditions
		min.	typ.	max.		

DC Characteristics

Breakdown voltage	$V_{(BR)}$	3	–	–	V	$I_{(BR)} = 10\text{ }\mu\text{A}$
Forward voltage	V_F	–	0.4	0.5	V	$I_F = 100\text{ }\mu\text{A}$

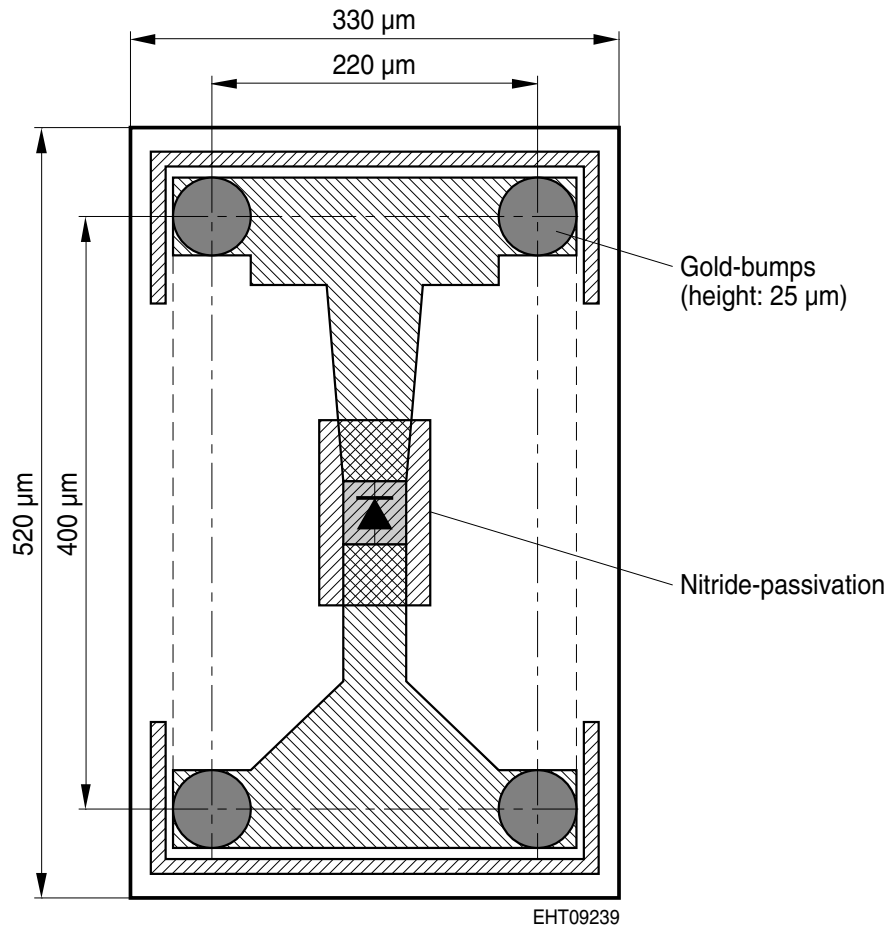
AC Characteristics

Diode capacitance ¹⁾	C_T	–	30	–	fF	$V_R = 0\text{ V}$
Forward resistance	R_F	–	7	10	Ω	$I_F = 10\text{ mA}$

¹⁾ Simulated values test conditions t.b.f.

Chip Layout

FLIP CHIP 1



Sorts of Packing

Package outlines for tubes, trays etc. are contained in our Data Book "Package Information".

Dimensions in mm